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ChuanKang Liang, Student Member, IEEE, And Behzad Razavi, Fellow, IEEE Abstract—This Paper Proposes A Simulation-based Modeling Methodology That Provides Greater flexibility In The Design And Apr 7th, 2024.
IEEE JOURNAL OF SOLID-STATE CIRCUITS, VOL. 44, NO. 12 ...Payam Heydari, Senior Member, IEEE Abstract—Integration Of Multi-mode Multi-band Transceivers On A Single Chip Will Enable Low-cost Millimeter-wave Systems For Next-generation Automotive Radar Sensors. The first Dual-band Millimeter-wave Transceiver Operating In The 22–29-GHz And 77–81 Jun 10th, 2024IEEE JOURNAL OF SOLID-STATE CIRCUITS, VOL. 49, NO. 8 ...IEEE JOURNAL OF SOLID-STATE CIRCUITS, VOL. 49, NO. 8, AUGUST 2014 1739 A 7.1 MW 1 GS/s ADC With 48 DB SNDR At Nyquist Rate Sedigheh Hashemi And Behzad Razavi, Fellow, IEEE Abstract—A Two-stage Pipelined ADC Employs A Double-sam- Pling Jun 1th, 20242398 IEEE JOURNAL OF SOLID-STATE CIRCUITS, VOL. 40, NO. …Higher SNDR. The Modulator Achieves 82-dB Dynamic Range And 81-dB Peak SNDR In The A-weighted Audio Signal Bandwidth With An OSR Of 64. The Total Power Consumption Of The Modulator Is 1 MW From A 0.6-V Supply. The Prototype Occupies 2.9 Mm2 Using A 0.35- M CMOS Technology. Index Terms—Del Jan 5th, 2024.
IEEE JOURNAL OF SOLID-STATE CIRCUITS, VOL. 36, NO. 11 ...B. Quadrature Clock Generator The PLL Provides Two 1-GHz 50% Duty-cycle Clocks,clk And Clkq In Fig. 1, That Are Phase Shifted With Respect To One An-other By 90 . As Noted In The Introduction, Quadrature Clocks Simplify The Generation Of The Local 2-GHz Clocks That Are Re-quired In Sections Of The SOC That Are Double-pumped In Order Jan 8th, 20241944 IEEE JOURNAL OF SOLID-STATE CIRCUITS, VOL. 41, NO. …A Compact Switched-Capacitor Regulated Charge Pump Power Supply B. Robert Gregoire, Member, IEEE Abstract—A CMOS Switched-capacitor Reference Is Combined With A Switched-capacitor Voltage Doubling Charge Pump To Pro-duce A Compact Regulated 3.2-V Power Supply From An Input That Ranges From 1.8 To 3.5 V. It Can Supply Up To 6 MA At Minimum Input. May 7th, 20241186 IEEE JOURNAL OF SOLID-STATE CIRCUITS, VOL. 45, NO. …1188 IEEE JOURNAL OF SOLID-STATE CIRCUITS, VOL. 45, NO. 6, JUNE 2010 Fig. 4. Comparison Between (a) A Conventional Current-Switch FFE And (b) A Charge-Injection FFE When Data Pattern Is '011'. Fig. 5. Simulated (a) Current, (b) Voltage, And (c) Current In Fig. 1 When An Isolat Apr 4th, 2024.
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2021 IEEE IEEE SOLID-STATE CIRCUITS SOCIETYBasic Design Approaches To Accelerating Deep Neural Networks 7:20 Am – T8: On-Chip Interconnects: Basic Concepts, Designs, & Future Opportunities 7:40 Am – T9: Designing Amplifiers For Stability 8:00 Am – T10: Fundamentals Of Fully Integrated Voltage Regulator Mar 6th, 2024IEEE JOURNAL OF SOLID-STATE CIRCUITS 1 Integrated Cold ...Source Of Energy, And Unlike Solar Power, It Can Be Harnessed Irrespective Of Illumination Conditions. As Such, Body Heat Is An Ideal Energy Source For Self-powered Wearable Devices [1]. Thermal Energy Can Be Converted To Electrical Energy Using Thermoelectric Generators (TEG), The Solid- May 3th, 2024IEEE JOURNAL OF SOLID-STATE CIRCUITS 1 Hybrid ...Bonding And Use This Technology To Create A Multiphase, 40-MHz Buck Converter Supporting A 20-V Input Supply. Our Au–Au Interconnects Between The GaN Chiplet And The CMOS Substrate Are 30 µm In Diameter, And The Die-to-die Standoff Distance Is 50 µm, Resulting In An Interconnect Inductanc Jun 10th, 2024.
IEEE JOURNAL OF SOLID-STATE CIRCUITS 1 In-Memory ...IEEE JOURNAL OF SOLID-STATE CIRCUITS 1 In-Memory Computation Of A Machine-Learning Classifier In A Standard 6T SRAM Array Jintao Zhang, Student Member, IEEE, Zhuo Wang, Member, IEEE, And Naveen Verma Member, IEEE, Abstract—This Paper Presents A Machine-learning Classifier Where Computat Jun 4th, 2024